

April 2009

MOC215M, MOC216M, MOC217M Small Outline Surface Mount Phototransistor Optocouplers

Features

- U.L. recognized (File #E90700, Volume 2)
- VDE recognized (File #136616) (add option "V" for VDE approval, i.e, MOC205VM)
- Convenient plastic SOIC-8 surface mountable package style
- Low LED input current required for easier logic interfacing
- Standard SOIC-8 footprint, with 0.050" lead spacing
- Compatible with dual wave, vapor phase and IR reflow soldering
- High input-output isolation of 2500 V_{AC(rms)} guaranteed

Applications

- Low power logic circuits
- Interfacing and coupling systems of different potentials and impedances
- Telecommunications equipment
- Portable electronics

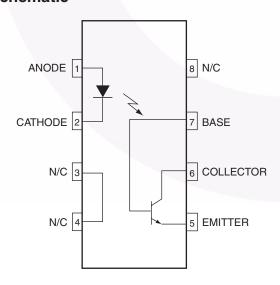
Description

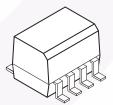
These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high density applications, and eliminate the need for throughthe-board mounting.

Marking Information

- MOC215M = 215
- MOC216M = 216
- MOC217M = 217

Schematic





Absolute Maximum Ratings (T_A = 25°C Unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit
EMITTER			
I _F	Forward Current – Continuous	60	mA
I _F (pk)	Forward Current – Peak (PW = 100µs, 120pps)	1.0	Α
V _R	Reverse Voltage	6.0	V
P _D	LED Power Dissipation @ T _A = 25°C	90	mW
	Derate above 25°C	0.8	mW/°C
DETECTOR			
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	70	V
V _{ECO}	Emitter-Collector Voltage	7.0	V
I _C	Collector Current-Continuous	150	mA
P _D	Detector Power Dissipation @ T _A = 25°C	150	mW
	Derate above 25°C	1.76	mW/°C
TOTAL DEVICE			
V _{ISO}	Input-Output Isolation Voltage (f = 60Hz, t = 1 min.) ⁽¹⁾⁽²⁾	2500	Vac(rms)
P _D	Total Device Power Dissipation @ T _A = 25°C	250	mW
	Derate above 25°C	2.94	mW/°C
T _A	Ambient Operating Temperature Range	-40 to +100	°C
T _{stg}	Storage Temperature Range	-40 to +125	°C

Notes:

- 1. Isolation Surge Voltage, V_{ISO} , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.

Electrical Characteristics ($T_A = 25$ °C unless otherwise specified)

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER						1
V _F	Forward Voltage	I _F = 1.0mA		1.07	1.3	V
I _R	Reverse Leakage Current	V _R = 6.0V		0.001	100	μΑ
С	Capacitance			18		pF
DETECTO	OR .		'			'
I _{CEO}	Collector-Emitter Dark Current	$V_{CE} = 5.0V, T_A = 25^{\circ}C$		1.0	50	nA
		$V_{CE} = 5.0V, T_A = 100^{\circ}C$		1.0		μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 100μA	30	100		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100μA	7.0	10		V
C _{CE}	Collector-Emitter Capacitance	f = 1.0MHz, V _{CE} = 0		7.0		pF
COUPLE						
CTR	Output Collector Current ⁽⁴⁾ MOC215M MOC216M MOC217M	$I_F = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}$	20 50 100			%
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100\mu A, I_F = 1.0mA$			0.4	V
t _{on}	Turn-On Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega, \text{ (Fig. 10)}$		4.0		μs
t _{off}	Turn-Off Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 10)}$		4.0		μs
t _r	Rise Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 10)}$		3.0		μs
t _f	Fall Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 10)}$		3.0		μs
V _{ISO}	Input-Output Isolation Voltage ⁽¹⁾⁽²⁾⁽³⁾	f = 60 Hz, t = 1.0 min.	2500			Vac(rms)
R _{ISO}	Isolation Resistance ⁽²⁾	V _{I-O} = 500V	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance ⁽²⁾	V _{I-O} = 0, f = 1.0MHz		0.2		pF

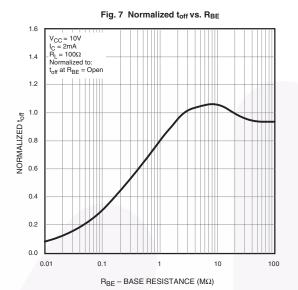
^{*}Typical values at T_A = 25°C

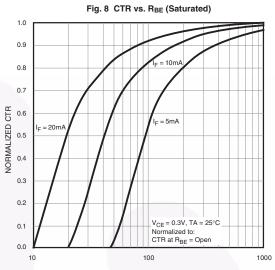
Notes:

- 1. Isolation Surge Voltage, V_{ISO} , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.
- 3. V_{ISO} rating of 2500 $V_{AC(rms)}$ for t = 1 min. is equivalent to a rating of 3,000 $V_{AC(rms)}$ for t = 1 sec.
- 4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

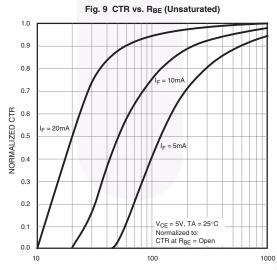
Typical Performance Curves Fig. 1 LED Forward Voltage vs. Forward Current Fig. 2 Output Curent vs. Input Current 1.8 $_{1c}$ – OUTPUT COLLECTOR CURRENT (NORMALIZED) 1.6 V_F - FORWARD VOLTAGE (V) V_{CE} = 5V NORMALIZED TO I_E = 10mA 1.3 T_A = 25°C 1.1 1.0 10 I_F – LED FORWARD CURRENT (mA) 0.01 0.1 10 I_F – LED INPUT CURRENT (mA) Fig. 3 Output Current vs. Ambient Temperature Fig. 4 Output Current vs. Collector-Emitter Voltage CURRENT (NORMALIZED) - OUTPUT COLLECTOR CURRENT (NORMALIZED) 1.2 1.0 · OUTPUT COLLECTOR 0.8 0.6 0.4 0.2 I_F= 10mA NORMALIZED TO V_{CE} = 5V NORMALIZED TO TA = 25°C 0.0 V_{CE} – COLLECTOR-EMITTER VOLTAGE (V) T_A – AMBIENT TEMPERATURE (°C) Fig. 5 Dark Current vs. Ambient Temperature Fig. 6 Normalized ton vs. RBE 10000 4.0 $V_{CC} = 10V$ I_{CEO} - COLLECTOR -EMITTER DARK CURRENT (nA) $I_C = 2mA$ V_{CE} = 10V 3.5 1000 $R_L = 100\Omega$ NORMALIZED TO: t_{on} AT R_{BE} = OPEN 3.0 NORMALIZED ton 100 2.5 2.0 1.5 1.0 0.5 0.0 0.1 0.01 100 40 20 ${\rm R_{BE}}-{\rm \ BASE}$ RESISTANCE (M Ω) T_A – AMBIENT TEMPERATURE (°C)

Typical Performance Curves (Continued)





 R_{BE} – BASE RESISTANCE ($k\Omega$)



 $R_{\mbox{\footnotesize{BE}}}$ – BASE RESISTANCE (k Ω)

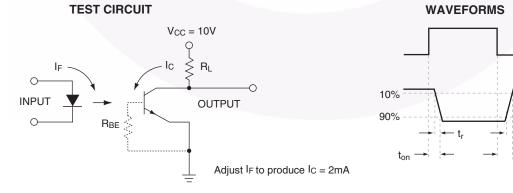


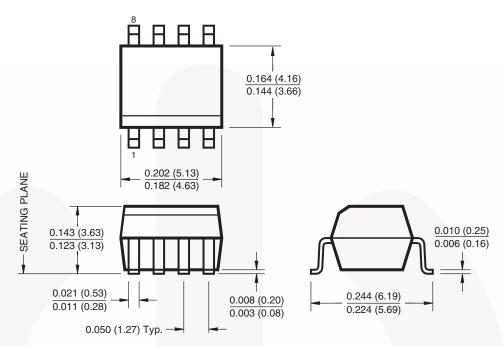
Figure 10. Switching Time Test Circuit and Waveforms

INPUT PULSE

OUTPUT PULSE

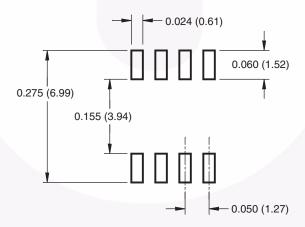
Package Dimensions

8-pin SOIC Surface Mount



Lead Coplanarity: 0.004 (0.10) MAX

Recommended Pad Layout



Dimensions in inches (mm).

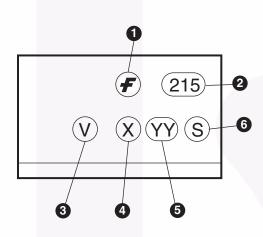
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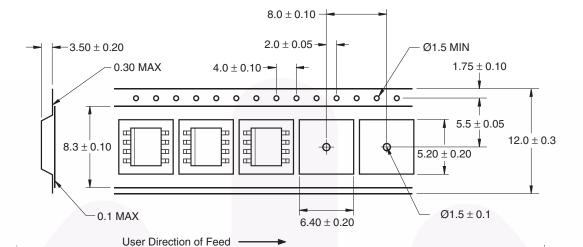
Option	Order Entry Identifier	Description	
V	V	VDE 0884	
R2	R2	Tape and reel (2500 units per reel)	
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)	

Marking Information



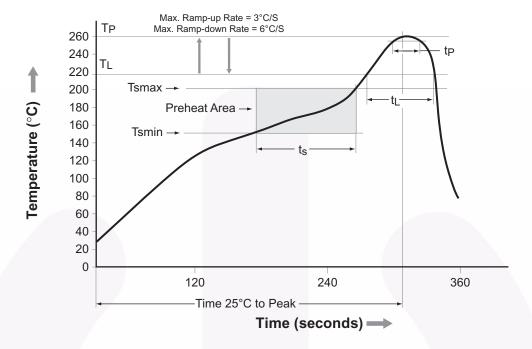
Defini	tions	
1	Fairchild logo	
2	Device number	
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)	
4	One digit year code, e.g., '8'	
5	Two digit work week ranging from '01' to '53'	
6	Assembly package code	

Carrier Tape Specifications



Dimensions in mm

Reflow Profile



Profile Freature	Pb-Free Assembly Profile	
Temperature Min. (Tsmin)	150°C	
Temperature Max. (Tsmax)	200°C	
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds	
Ramp-up Rate (t _L to t _P)	3°C/second max.	
Liquidous Temperature (T _L)	217°C	
Time (t _L) Maintained Above (T _L)	60-150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t _P) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T _P to T _L)	6°C/second max.	
Time 25°C to Peak Temperature	8 minutes max.	





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Definition of Terms			
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